

AMENDMENTS TO THE CLAIMS

This listing of claims will replace all prior versions and listings of claims in the application:

LISTING OF CLAIMS:

1. (currently amended): A capacitor comprising:

an approximately plate-shaped capacitor main body having a first surface on which a semiconductor device having surface-connecting terminals is to be mounted and a second surface; and

a plurality of electrically conductive vias penetrating the capacitor main body between the first and second surfaces for connection with the surface-connecting terminals;

wherein the plurality of electrically conductive vias all have a straight shape.

2. (currently amended): A semiconductor device equipped capacitor assembly comprising:

a semiconductor device having surface-connecting terminals; and

a capacitor having an approximately plate-shaped capacitor main body having a first surface on which the semiconductor device is mounted and a second surface and a plurality of electrically conductive vias penetrating the capacitor main body between the first and second surfaces and connected to the surface-connecting terminals, the plurality of electrically conductive vias all having a straight shape.

3. (currently amended): A capacitor equipped substrate assembly comprising:

a substrate having surface-connecting pads; and

a capacitor having an approximately plate-shaped capacitor main body having a first surface and a second surface at which the capacitor is mounted on the substrate and a plurality of electrically conductive vias penetrating the capacitor main body between the first and second surfaces and connected to the surface-connecting pads, the plurality of electrically conductive vias all having a straight shape,

wherein the thermal expansion coefficient of the capacitor main body is smaller than that of the substrate.

4. (currently amended): An assembly comprising:

a semiconductor device having surface-connecting terminals;

a substrate having surface-connecting pads; and

a capacitor having an approximately plate-shaped capacitor main body having a first surface on which the semiconductor device is mounted and a second surface at which the capacitor main body is mounted on the substrate and a plurality of electrically conductive vias penetrating the capacitor main body between the first and second surfaces and connected to the surface-connecting terminals and the surface-connecting pads, all of the plurality of electrically conductive vias having a straight shape,

wherein the thermal expansion coefficient of the capacitor main body is smaller than that of the substrate.

5. (original): An interposer comprising:

an interposer main body having a first surface on which a semiconductor device having surface-connecting terminals is mounted and a second surface formed with a recess;

a plurality of interposer main body side electrically conductive vias penetrating the interposer main body between the first surface and a bottom surface of the recess and connected to the surface-connecting terminals; and

a capacitor disposed in the recess and having front and rear surfaces and a plurality of capacitor side electrically conductive vias passing through the front and rear surfaces and connected to the interposer main body side electrically conductive vias.

6. (withdrawn): An interposer according to claim 5, further comprising, within the interposer main body, a plurality of short electrically conductive ground vias passing through the first surface and an electrically conductive via pitch changing layer, at least a part of the short electrically conductive ground vias being electrically connected to ground vias of the capacitor side electrically conductive vias by way of the electrically conductive via pitch-changing layer.

7. (withdrawn): An interposer according to claim 5, further comprising, within the interposer main body, a plurality of short electrically conductive power vias passing through the first surface and an electrically conductive via pitch-changing layer, at least a part of the short electrically conductive power vias being electrically connected to power vias of the capacitor side electrically conductive vias by way of the electrically conductive via pitch-changing layer.

8. (original): A semiconductor device equipped interposer assembly comprising:
a semiconductor device having surface-connecting terminals; and
an interposer having an approximately plate-shaped interposer main body having a first surface on which the semiconductor device having surface-connecting terminals is mounted and a second surface formed with a recess, a plurality of interposer main body side electrically

conductive vias penetrating the interposer main body between the first surface and a bottom surface of the recess and connected to the surface-connecting terminals, and a capacitor disposed in the recess and having front and rear surfaces and a plurality of capacitor side electrically conductive vias extending through the front and rear surfaces and connected to the interposer main body side electrically conductive vias.

9. (original): An interposer equipped substrate assembly comprising:

a substrate having surface-connecting terminals; and

an interposer having an approximately plate-shaped interposer main body having a first surface and a second surface formed with a recess, the interposer main body being mounted at the second surface on the substrate, the interposer further having a plurality of interposer main body side electrically conductive vias penetrating the interposer main body between the first and second surfaces and connected to the surface-connecting terminals and a capacitor disposed in the recess and having front and rear surfaces and a plurality of capacitor side electrically conductive vias passing through the front and rear surfaces and connected to the interposer main body side electrically conductive vias.

10. (original): An assembly comprising:

a semiconductor device having surface-connecting terminals;

a substrate having surface-connecting pads; and

an interposer having an approximately plate-shaped interposer main body having a first surface on which the semiconductor device is mounted and a second surface formed with a recess, the interposer main body being mounted at the second surface on the substrate, the

interposer further having a plurality of interposer main body side electrically conductive vias penetrating the interposer main body between the first surface and a bottom surface of the recess and connected to the surface-connecting terminals and a capacitor disposed in the recess and having front and rear surfaces and a plurality of capacitor side electrically conductive vias passing through the front and rear surfaces and connected to the interposer main body side electrically conductive vias and the surface connecting pads.

Claims 11-22 (canceled).

23. (new): A capacitor comprising:

an approximately plate-shaped capacitor main body having a first ceramic surface on which a semiconductor device having surface-connecting terminals is to be mounted and a second surface; and

a plurality of electrically conductive vias penetrating the capacitor main body between the first and second surfaces for connection with the surface-connecting terminals.

24. (new): A semiconductor device equipped capacitor assembly comprising:

a semiconductor device having surface-connecting terminals; and

a capacitor having an approximately plate-shaped capacitor main body having a first ceramic surface on which the semiconductor device is mounted and a second surface and a plurality of electrically conductive vias penetrating the capacitor main body between the first and second surfaces and connected to the surface-connecting terminals.

25. (new): A capacitor equipped substrate assembly comprising:

a substrate having surface-connecting pads; and

a capacitor having an approximately plate-shaped capacitor main body having a first ceramic surface and a second surface at which the capacitor is mounted on the substrate and a plurality of electrically conductive vias penetrating the capacitor main body between the first and second surfaces and connected to the surface-connecting pads.

26. (new): An assembly comprising:

a semiconductor device having surface-connecting terminals;

a substrate having surface-connecting pads; and

a capacitor having an approximately plate-shaped capacitor main body having a first ceramic surface on which the semiconductor device is mounted and a second surface at which the capacitor main body is mounted on the substrate and a plurality of electrically conductive vias penetrating the capacitor main body between the first and second surfaces and connected to the surface-connecting terminals and the surface-connecting pads.